# **EFC6601R**

# N-Channel Power MOSFET 24V, 13A, 11.5mΩ, Dual EFCP



http://onsemi.com

#### **Features**

- 2.5V drive
- · Common-drain type
- · 2KV ESD HBM

- · Protection diode in
- · Halogen free compliance

# **Specifications**

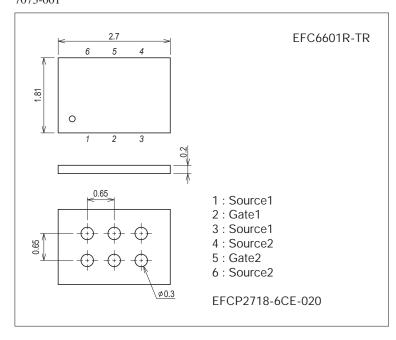
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	VSSS		24	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±12	V
Source Current (DC)	IS		13	А
Source Current (Pulse)	ISP	PW≤10μs, duty cycle≤1%	60	А
Total Dissipation	PT	When mounted on ceramic substrate (5000mm <sup>2</sup> ×0.8mm)	2.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Package Dimensions**

unit : mm (typ) 7073-001



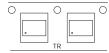
# **Product & Package Information**

• Package : EFCP

• JEITA, JEDEC :-

• Minimum Packing Quantity : 5,000 pcs./reel

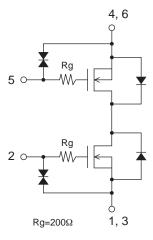
#### Taping Type: TR



# Marking



### **Electrical Connection**



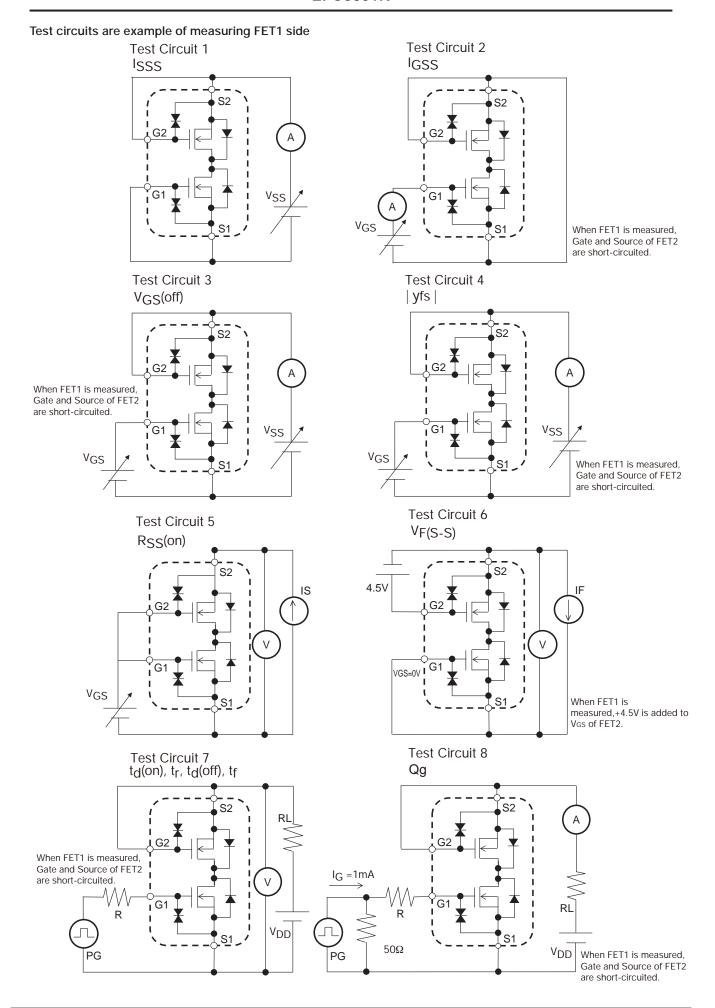
# EFC6601R

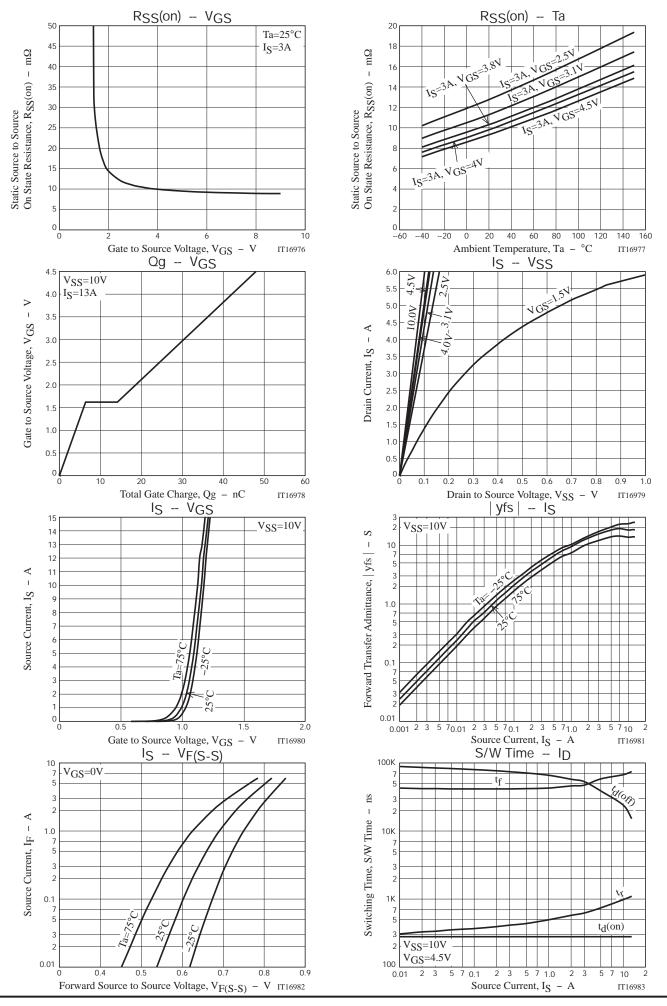
# Electrical Characteristics at Ta=25°C

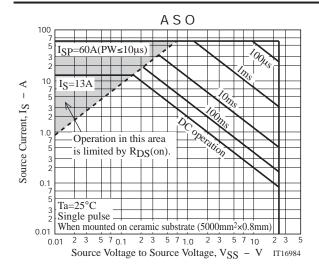
Parameter	Cumbal	Conditions		Ratings			Linit
Parameter	Symbol			min	typ	max	Unit
Source-to-Source Breakdown Voltage	V(BR)SSS	IS=1mA, VGS=0V	Test Circuit 1	24			V
Zero-Gate Voltage Source Current	ISSS	V <sub>SS</sub> =20V, V <sub>GS</sub> =0V	Test Circuit 1			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VSS=0V	Test Circuit 2			±1	μΑ
Cutoff Voltage	VGS(off)	V <sub>SS</sub> =10V, I <sub>S</sub> =1mA	Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	yfs	VSS=10V, IS=3A	Test Circuit 4		15.5		S
Static Source-to-Source On-State Resistance	R <sub>SS</sub> (on)1	I <sub>S</sub> =3A, V <sub>GS</sub> =4.5V	Test Circuit 5	6.6	9.5	11.5	mΩ
	R <sub>SS</sub> (on)2	I <sub>S</sub> =3A, V <sub>GS</sub> =4.0V	Test Circuit 5	7.0	10	12	mΩ
	RSS(on)3	I <sub>S</sub> =3A, V <sub>GS</sub> =3.8V	Test Circuit 5	7.3	10.5	13	mΩ
	RSS(on)4	IS=3A, VGS=3.1V	Test Circuit 5	8.0	11.5	15	mΩ
	RSS(on)5	IS=3A, VGS=2.5V	Test Circuit 5	9.0	13	17	mΩ
Turn-ON Delay Time	t <sub>d</sub> (on)		Test Circuit 7		280		ns
Rise Time	t <sub>r</sub>	Vpp 10V Vpp 4 EV Ip 24			630		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>S</sub> =3A			53000		ns
Fall Time	tf				47000		ns
Total Gate Charge	Qg	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>S</sub> =13A	Test Circuit 8		48		nC
Forward Source-to-Source Voltage	V <sub>F</sub> (S-S)	I <sub>S</sub> =3A, V <sub>GS</sub> =0V	Test Circuit 6		0.76	1.2	V

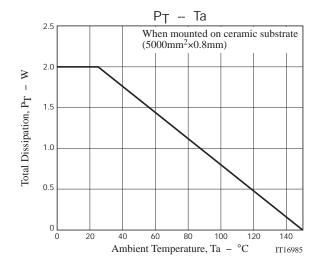
# Ordering Information

Device	Package	Shipping	memo	
EFC6601R-TR	EFCP	5,000pcs./reel	Pb Free and Halogen Free	





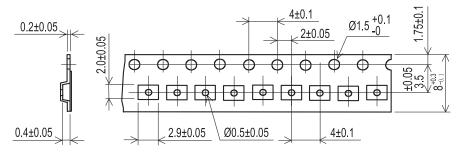




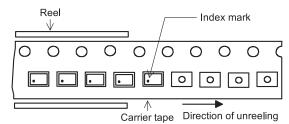
## **Taping Specification**

#### EFC6601R-TR

- 1. Taping Configuration
  - 1-1 .Carrier Tape Size (unit:mm)

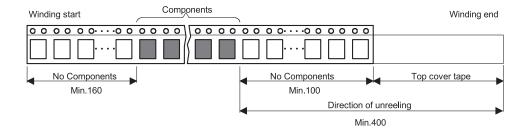


# 1-2 .Device Placement Direction



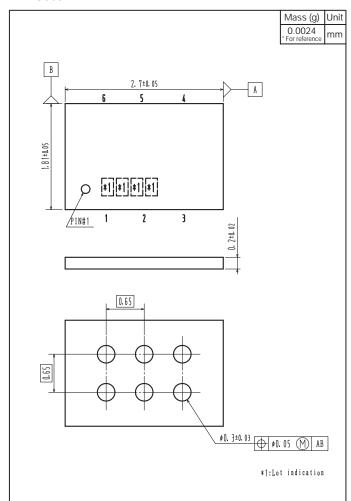
Packing type····TR

#### 1-3 .Leader portion and Trailer portion (unit:mm)

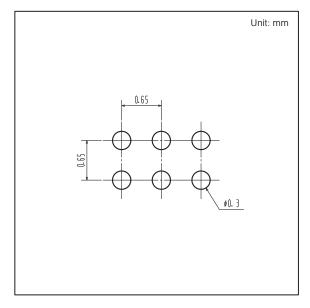


# **Outline Drawing**

EFC6601R-TR



# Land Pattern Example



Note on usage: Since the EFC6601R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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